

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co m m e n t s	Er r o r D e f i n i t i o n	Erro rs
11	BRS	L79	128	@pd<=19980618 and (1 and 19)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 10:09			0
12	BRS	L85	139	73 not 79	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 11:18			0
13	BRS	L91	81	1 same wetting	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 11:19			0
14	BRS	L97	98053	@pd<=19980618 and (91and 7)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 12:35			0
15	BRS	L10 3	64	@pd<=19980618 and 91	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 11:21			0
16	BRS	L73	161	@pd<=19980618 and (1 and 13)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 11:26			0
17	BRS	L10 9	1092	(DROP\$4 OR DRIP\$4 OR FLOWING OR "FLOW RATE") same ((DI adj water) or "DEIONIZED WATER" OR water) same (rinsing or cleaning or washing) same (substrate or wafer or semiconductor)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 12:28			0
18	BRS	L11 5	745	@pd<=19980618 and 109	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 12:41			0
19	BRS	L13 3	21	19 AND 115	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 12:41			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co m m e n t s	Er r o r D e f i n i t i o n	Erro rs
20	BRS	L12 1	60	7 AND 115	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 13:17			0
21	BRS	L12 7	154	13 AND 115	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 13:18			0

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TITLE: Method for washing wafers

ISD:
19950606

DEPR:
The support rods 43 of the fork 41 are washed and dried while the wafers W are kept in the **water washing** vessel 20 (Step 105). While scanning the **washing** nozzles 50 at a speed of 10 mm/second, pure **water** is jetted to the **wafer** support rods 43 through the nozzles 50 at a **flow rate** of 0.7-10 liters/minute.

CCOR:
134/25.4

CCXR:
134/15

CCXR:
134/25.1

CCXR:
134/26

CCXR:
134/32

CCXR:
134/34

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co m m e n t s	Er r o r D e f i n i t i o n	Erro rs
1	BRS	L1	2274	(plasma or etching) same ((DI adj water) or water) same (rinsing or wetting or cleaning or washing) same (substrate or wafer or semiconductor)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 12:25			0
2	BRS	L7	114730	438/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 09:56			0
3	BRS	L13	31763	134/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 09:56			0
4	BRS	L19	15203	216/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 09:56			0
5	BRS	L25	37	(ml or milliliter) same 1	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 09:57			0
6	BRS	L49	0	25 and 13	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 09:58			0
7	BRS	L55	2	25 and 19	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 09:58			0
8	BRS	L43	8	25 and 7	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 09:59			0
9	BRS	L61	511	1 and 7	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 10:07			0
10	BRS	L67	295	@pd<=19980618 and 61	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/09/25 11:19			0